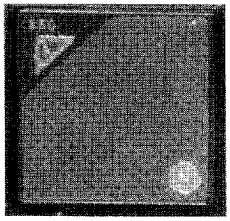
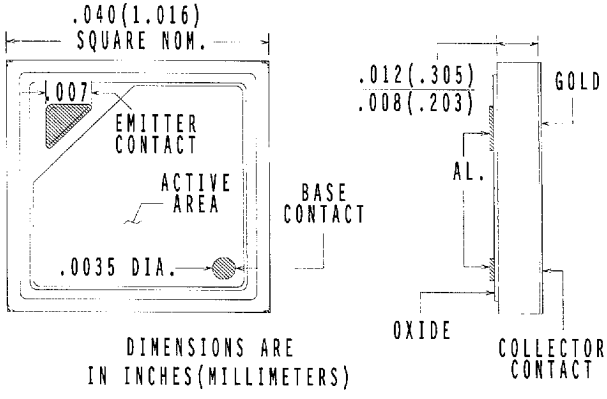
NPN Silicon Phototransistor Chip
Type OPC260





Features

- 2.7 times the active area of OPC200
- More sensitive at low light levels
- Active area centered on chip

Description

Optek Technology photosensor chips are fabricated using the latest silicon planar diffused technology and are silicon nitride passivated for long term stability. All photosensors have an anti-reflective coating over the active area to ensure maximum absorption of irradiated light. Chips can be specially probed for custom requirements.

Optek chip warranty excludes any damage resulting from improper bonding or alloying techniques.

Packaging Options

OPC260VP Vials
OPC260TP Sawn on Tape
OPC260WP Waffle Pack
OPC260SP Unsawn Slice
Special packaging and testing available upon request. Special transistor arrays available upon request

Replaces

OPC60X

Absolute Maximum Ratings[1] (T_A = 25° C unless otherwise noted)

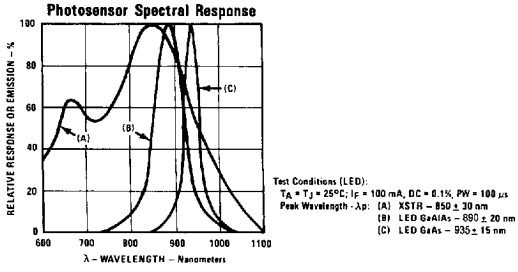
Operating Temperature ..... -40° C to +85° C
Storage Temperature ..... -65° C to +150° C
Collector-Emitter Voltage ..... 30 V
Emitter-Collector Voltage ..... 5.0 V
Power Dissipation ..... 50 mW[2]

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30	60		V	I_C = 100µA
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0	7.5		V	I_E = 100µA
I_{CEO}	Collector Dark Current		<1	100	nA	V_{CE} = 10.0V, Φ=0µW
R_λ	Responsivity		0.25		A/W	V_{CE}=5V, Φ=10µW[3]
h_{FE}	Current Gain	50				V_{CE} = 5.0V, I_C =1mA

Notes: (1) All maximum ratings are determined with the chip mounted on a dimpled TO-18 header using Optek techniques. (2) Maximum power dissipation is a function of the package in which the chip is housed and the environment in which the assembled package will be used. (3) Light source is a GaAs LED, λ_P = 935 nm, typical.

Typical Performance Curves



EMITTER & PHOTOSENSOR CHIPS

6798580 0002732 9T9